



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

2SA2222SG — PNP Epitaxial Planar Silicon Transistor — High-Current Switching Applications

Applications

- Relay drivers, lamp drivers, motor drivers

Features

- Adoption of MBIT process
- Low collector-to-emitter saturation voltage ($V_{CE(sat)} = -250\text{mV (typ.)}$)
- High-speed switching ($t_f = 22\text{ns (typ.)}$)
- Large current capacity ($I_C = -10\text{A}$)

Specifications

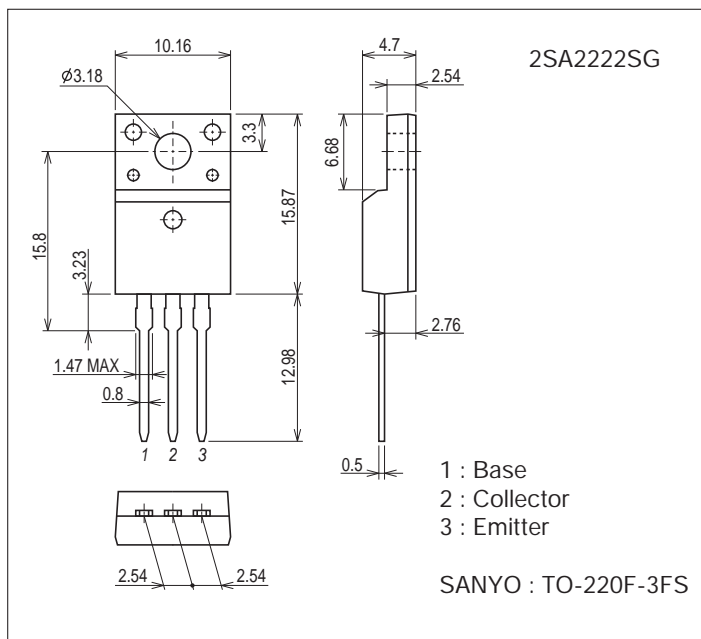
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		-50	V
Collector-to-Emitter Voltage	V_{CEO}		-50	V
Emitter-to-Base Voltage	V_{EBO}		-6	V
Collector Current	I_C		-10	A
Collector Current (Pulse)	I_{CP}		-13	A
Base Current	I_B		-2	A
Collector Dissipation	P_C	$T_c = 25^\circ\text{C}, P_T \leq 1\text{s}$	25	W
Junction Temperature	T_j		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Package Dimensions

unit : mm (typ)

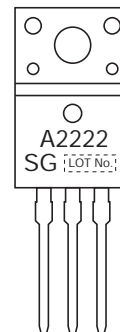
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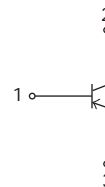
Product & Package Information

- Package : TO-220F-3FS
- JEITA, JEDEC : SC-67
- Minimum Packing Quantity : 50 pcs./magazine

Marking



Electrical Connection

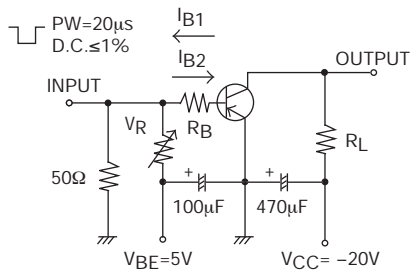


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Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=-40V, I_E=0A$			-10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4V, I_C=0A$			-10	μA
DC Current Gain	h_{FE}	$V_{CE}=-2V, I_C=-270mA$	150		450	
Gain-Bandwidth Product	f_T	$V_{CE}=-10V, I_C=-1A$		230		MHz
Output Capacitance	C_{ob}	$V_{CB}=-10V, f=1MHz$		115		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-6A, I_B=-300mA$		-250	-500	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-6A, I_B=-300mA$			-1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0A$	-50			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA, R_{BE}=\infty$	-50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0A$	-6			V
Turn-On Time	t_{on}	See specified Test Circuit.		40		ns
Storage Time	t_{stg}			240		ns
Fall Time	t_f			22		ns

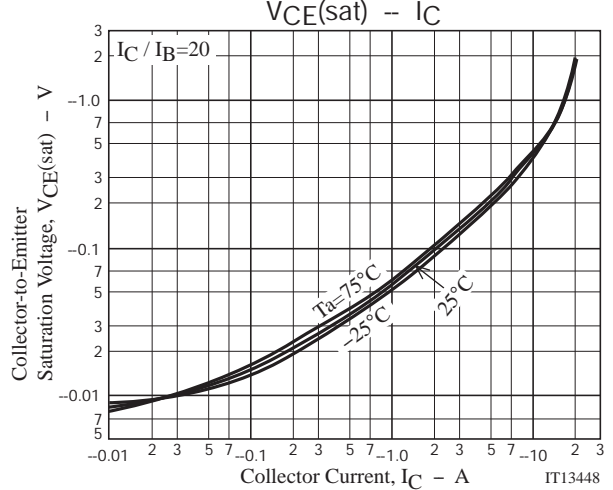
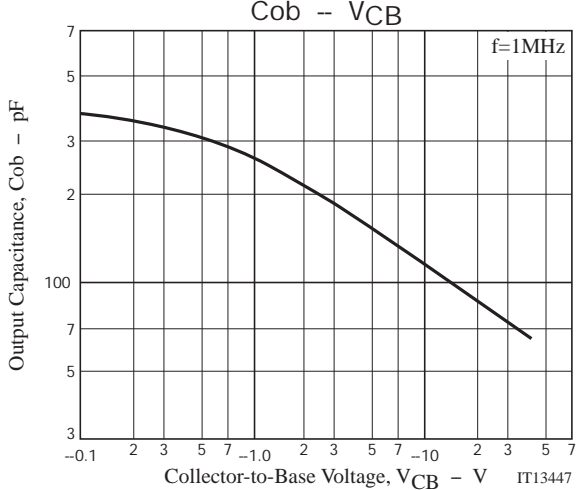
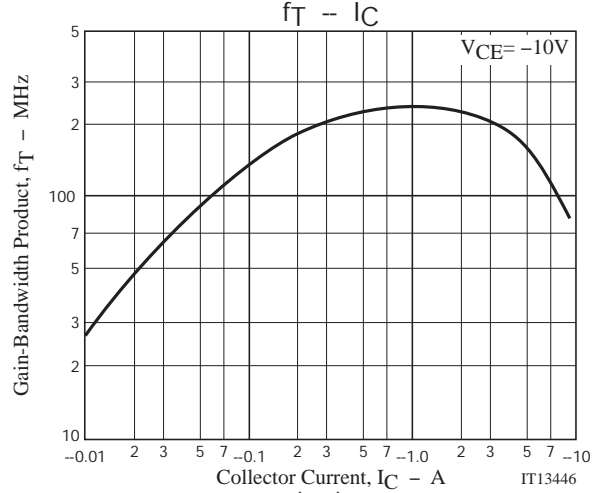
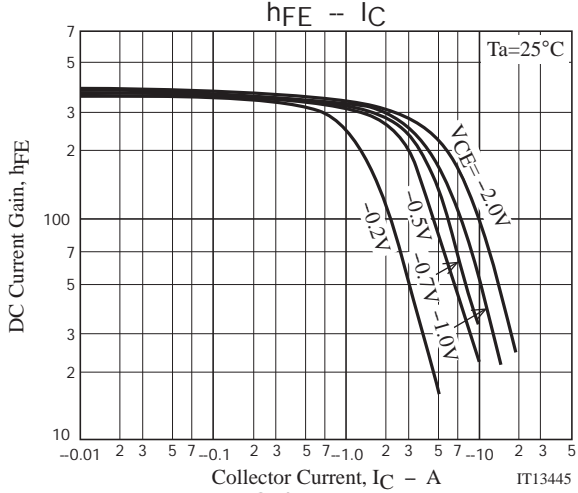
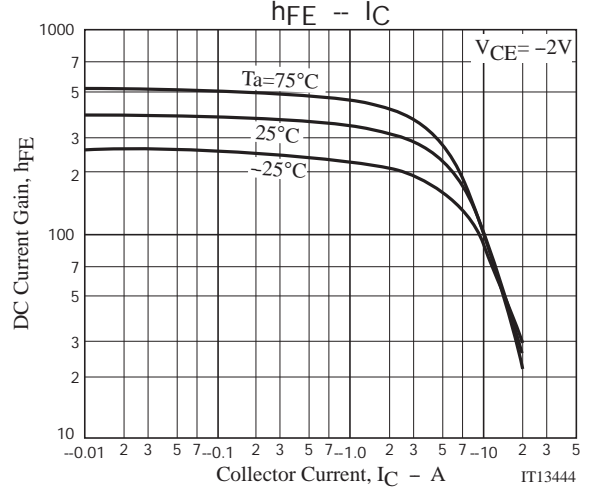
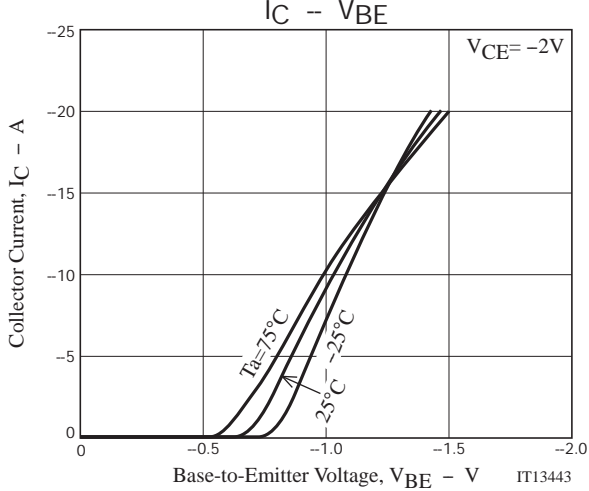
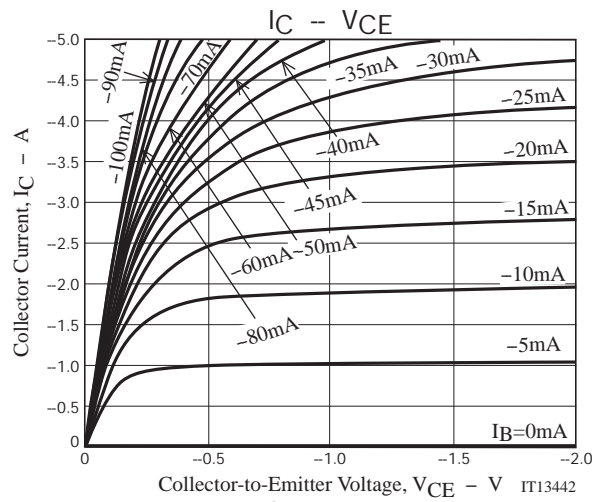
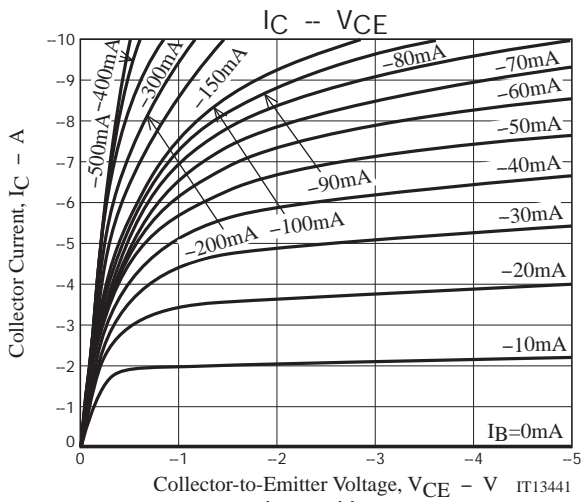
Switching Time Test Circuit

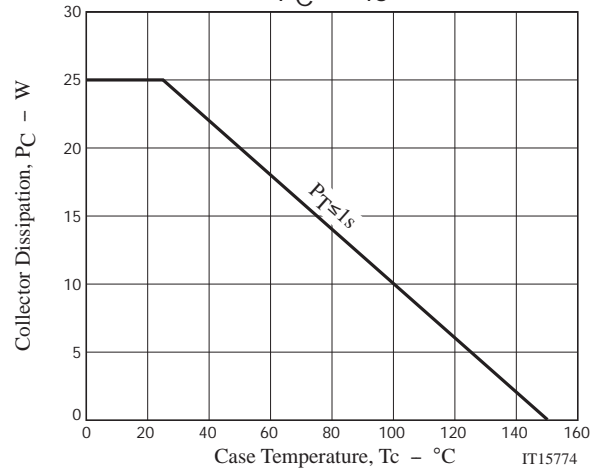
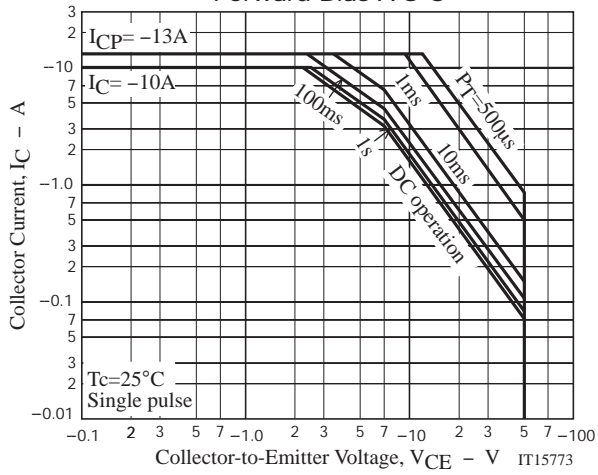
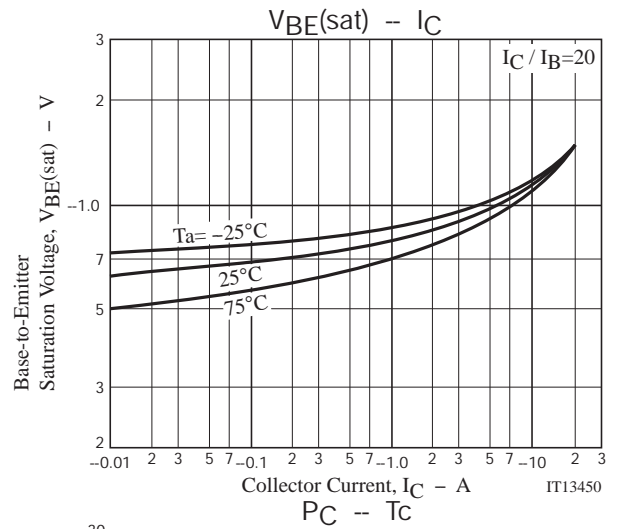
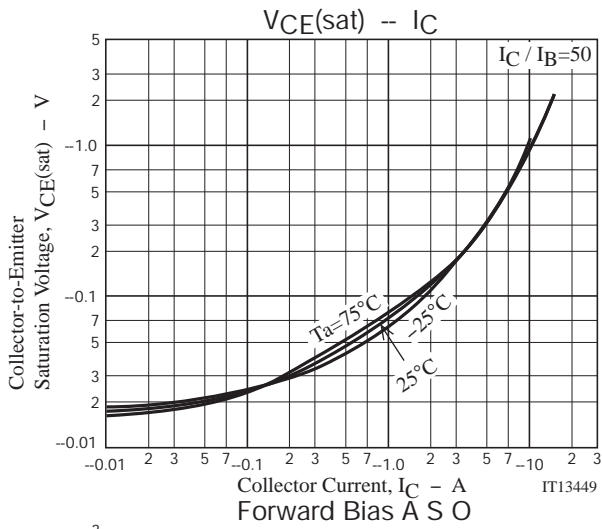


$$I_C = 20I_{B1} = -20I_{B2} = -5A$$

Ordering Information

Device	Package	Shipping	memo
2SA2222SG	TO-220F-3FS	50pcs./magazine	Pb Free





Magazine Specification

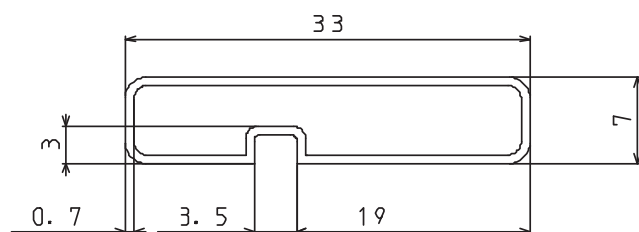
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1. Packing Format

Package Name	Magazine Name	Maximum Number of devices contained (pcs)			Packing format	
		Magazine	Inner box	Outer box	Inner BOX	Outer BOX
TO-220F-3FS	TO-220F	50	1,000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178

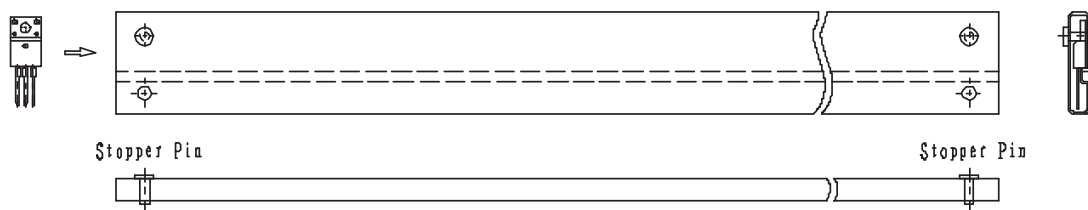
2. Magazine dimensions

(unit:mm)

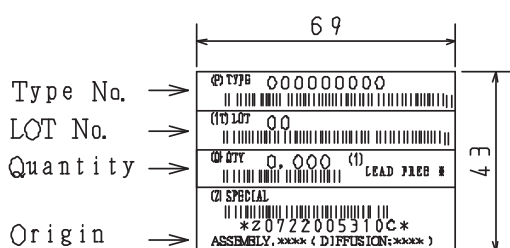


Tolerance=±0.3mm
 Thickness=0.7±0.2mm
 Length =532.5±2mm
 Material =PVC (Antistatic treatment)

3. Storage method to magazine

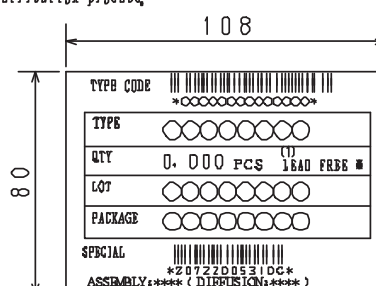


4. Inner box label (unit:mm)



5. Outer box label (unit:mm)

It is a label at the time of factory shipments.
 The form of a label may change in physical
 distribution process.



NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

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Outline Drawing

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